### Device Characterization Project #3 - April 18, 2003

NPN BJT CHARACTERIZATION

Due: April 25, 2003 at recitation (Rm. 26-310, 12:55 PM) (late project reports not accepted)

#### Please write your recitation session time on your project report.

In this project, you will characterize the current-voltage characteristics of an npn bipolar junction transistor (BJT). To do this, you will use the *MIT Microelectronics WebLab*. Refer to the User Manual for instructions on how to use the system.

Two identical npn BJTs are available in locations 4 and 5 of weblab. They are labeled "6.012 npn BJT." The terminal connection configuration is identical for both of them and is available on line. This exercise involves three separate phases: (i) measurement and graphing, (ii) SPICE model parameter extraction, and (iii) comparison of SPICE model with measurements. Take the measurements specified below. When you are happy with the results (as judged by the characteristics displayed through the web), download the data to your local machine for more graphing and further analysis. You will find useful to study the contents of *Appendix A* which describes the ideal model for the I-V characteristics of an npn BJT.

Important note: For all measurements, hold  $V_{BE}$  (or  $V_{BC}$ ) between 0 and 0.9 V, and  $V_{CE}$  between 0 and  $\pm 4 V$ .

Here is your assignment.

- 1. (10 points) Measure and download the common-emitter output characteristics of the BJT. This is a plot of  $I_C$  (linear scale) vs.  $V_{CE}$  (linear scale) with  $I_B$  as parameter, for positive  $V_{CE}$ . Do this for  $0 \le V_{CE} \le 4$  V and  $0 \le I_B \le 100 \ \mu A$  with  $\Delta I_B = 20 \ \mu A$ . In your local machine and using your favorite software tool, graph the output characteristics. Turn in a printout of this graph (graph 1).
- 2. (10 points) Measure and download the common-emitter transfer characteristics of the BJT in the forward active regime (also known as Gummel plot). This is a semilog plot of  $I_C$  and  $I_B$  (logarithmic scale) vs.  $V_{BE}$  (linear scale). Do this for  $V_{CE} = 2.5 V$ . In

your local machine graph the Gummel plot. Turn in a printout of this graph (graph 2). In a separate plot, graph the current gain of the bipolar transistor vs.  $I_C$ . This is a semilog plot of  $\beta_F = I_C/I_B$  (linear scale) vs.  $I_C$  (logarithmic scale). The lower end of the  $I_C$  scale should be  $I_C = 10^{-7} A$ . Turn in a printout of this graph (graph 3).

- 3. (10 points) Measure and download the reverse common-emitter output characteristics of the BJT. This is a plot of  $I_C$  (linear scale) vs.  $V_{CE}$  (linear scale) with  $I_B$  as parameter, for negative  $V_{CE}$ . Do this for  $-4 \leq V_{CE} \leq 0$  V and  $0 \leq I_B \leq 100 \ \mu A$ with  $\Delta I_B = 20 \ \mu A$ .. In your local machine graph the reverse output characteristics. Turn in a printout of this graph (graph 4).
- 4. (10 points) Measure and download the reverse common-emitter transfer characteristics of the BJT (also known as reverse Gummel plot). This is a plot of I<sub>E</sub> and I<sub>B</sub> (logarithmic scale) vs. V<sub>BC</sub> (linear scale). Do this for V<sub>EC</sub> = 2.5 V. In your local machine graph the reverse Gummel plot. Turn in a printout of this graph (graph 5). In a separate plot, graph the reverse current gain of the bipolar transistor vs. I<sub>E</sub>. This is a semilog plot of β<sub>R</sub> = I<sub>E</sub>/I<sub>B</sub> (linear scale) vs. I<sub>E</sub> (logarithmic scale). Turn in a printout of this graph (graph 6).
- 5. (15 points) From the forward and reverse Gummel plots, extract  $V_{BEon}$  and  $V_{BCon}$ , respectively. Define these voltages as the values of  $V_{BE}$  and  $V_{BC}$  that yield  $I_B = 10 \ \mu A$ . Derive  $V_{CEsat} = V_{BEon} V_{BCon}$ .
- 6. (15 points) From the forward and reverse Gummel plots, extract the SPICE parameters **IS**, **BF** and **BR**. Refer to Appendix A for the definitions and roles of these parameters.
- 7. (20 points) Using the SPICE parameter set just derived, play back the characteristics of the BJT and compare them with the measurement data. Construct the following graphs that include both measurements and SPICE model calculations. Use individual dots for the data points and continuous lines for model calculations.

graph 7: Common-emitter output characteristics in forward regime. Print this graph.

graph 8: Gummel plot in forward regime. Print this graph.

graph 9: Common-emitter output characteristics in reverse regime. Print this graph.

graph 10: Gummel plot in reverse regime. Print this graph.

- 8. (5 points) The SPICE model can by refined by accounting for the finite output conductance of the device. From the forward output characteristics, extract the SPICE parameter **VA**. Refer to Appendix A for the definition and role of this parameter.
- 9. (5 points) Replay the common-emitter output characteristics of the device in the forward regime using the SPICE model set that incorporates **VA** (see Appendix A). Turn in this graph (graph 11).

### Additional information and assorted advice

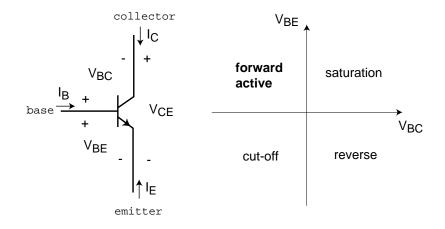
- For the SPICE parameter extraction portion of the exercise, there is no need to use an optimizer or any other fancy software. The ideal model does not match the experimental characteristics all that well. Simple extraction algorithms that you can devise should do an adequate job. Make sure the resulting values of the extracted parameters make physical sense.
- While it is not required for the report, it may be useful to download screenshots of your data from weblab. They serve as a useful reference for what your final graphs should look like.
- The required graphs need not be too fancy, just simply correct. They must have proper tickmarks, axis labeling and correct units. When there are several lines, each one should be properly identified (handwriting is OK).
- If you encounter problems with weblab or the MOSFETs, please e-mail the weblab TA, Niamh Waldron, Prof. del Alamo, or the weblab system manager, David Zych.
- You have to exercise care with these devices. Please do not apply a higher voltage than suggested. The BJTs are real and they can be damaged. If the characteristics look funny, try a different device and let us know.
- It will be to your advantage to make good use of the *Set-up* management functions that are built into the tool under the *File* menu (see manual).
- For research purposes, the system keeps a record of all logins and all scripts that each user executes.

# Note on collaboration policy

In carrying out this exercise (as in all exercises in this class), you may collaborate with somebody else that is taking the subject. In fact, collaboration is encouraged. However, this is not a group project to be divided among several participants. Every individual must have carried out the entire exercise, that means, using the web tool, graphing the data off line, and extracting suitable parameters. Everyone of these items contains a substantial educational experience that every individual must be exposed to. If you have questions regarding this policy, please ask the instructor. Prominently shown in your solutions should be the name of the person(s) you have collaborated with in this homework.

# Appendix A: BJT I-V characteristics

The conventions for terminal naming, voltage and current notations, and the various regimes of opeartion for an npn BJT are all shown below:



The ideal I-V characteristics of an npn BJT are given by the following set of equations:

$$I_C = I_S(\exp\frac{qV_{BE}}{kT} - \exp\frac{qV_{BC}}{kT}) - \frac{I_S}{\beta_R}(\exp\frac{qV_{BC}}{kT} - 1)$$

$$I_B = \frac{I_S}{\beta_F}(\exp\frac{qV_{BE}}{kT} - 1) + \frac{I_S}{\beta_R}(\exp\frac{qV_{BC}}{kT} - 1)$$

$$I_E = -\frac{I_S}{\beta_F}(\exp\frac{qV_{BE}}{kT} - 1) - I_S(\exp\frac{qV_{BE}}{kT} - \exp\frac{qV_{BC}}{kT})$$

In the forward active regime  $(V_{BE} > 0, V_{BC} < 0)$ , these equations simplify to:

$$I_C \simeq I_S \exp \frac{qV_{BE}}{kT}$$

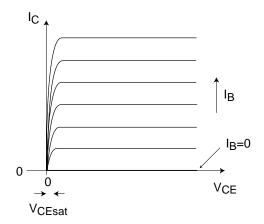
$$I_B \simeq \frac{I_S}{\beta_F} (\exp \frac{qV_{BE}}{kT} - 1)$$

$$I_E \simeq -I_S \exp \frac{qV_{BE}}{kT} - \frac{I_S}{\beta_F} (\exp \frac{qV_{BE}}{kT} - 1)$$

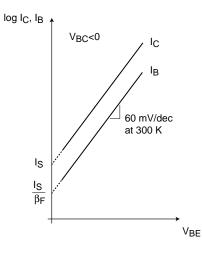
In the reverse regime  $(V_{BE} < 0, V_{BC} > 0)$ , the equations simplify to:

$$I_C \simeq -I_S \exp \frac{qV_{BC}}{kT} - \frac{I_S}{\beta_R} (\exp \frac{qV_{BC}}{kT} - 1)$$
$$I_B \simeq \frac{I_S}{\beta_R} (\exp \frac{qV_{BC}}{kT} - 1)$$
$$I_E \simeq I_S \exp \frac{qV_{BC}}{kT}$$

The common-emitter output characteristics of an ideal npn BJT look as in the figure below:



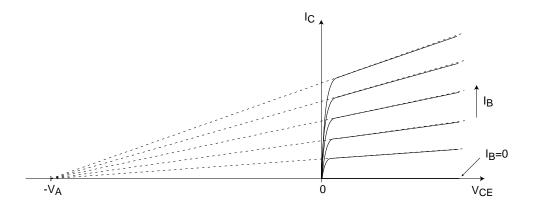
The common-emitter transfer characteristics (*Gummel plot*) of an ideal npn BJT look as in the figure below:



A more refined model includes the finite output conductance of the device (*Early effect*) through a new parameter called the Early voltage. In the forward active regime, the equation set becomes:

$$\begin{split} I_C &\simeq & I_S(1 + \frac{V_{CE}}{V_A}) \exp \frac{qV_{BE}}{kT} \\ I_B &\simeq & \frac{I_S}{\beta_F} (\exp \frac{qV_{BE}}{kT} - 1) \\ I_E &\simeq & -I_S(1 + \frac{V_{CE}}{V_A}) \exp \frac{qV_{BE}}{kT} - \frac{I_S}{\beta_F} (\exp \frac{qV_{BE}}{kT} - 1) \end{split}$$

One way of estimating the Early voltage is as indicated in the figure below:



The equations that describe the BJT map onto the SPICE model in the following way:

physics parameter	SPICE parameter
$I_S$	IS
$eta_F$	$\mathbf{BF}$
$\beta_R$	$\mathbf{BR}$
$V_A$	$\mathbf{V}\mathbf{A}$